

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application.

1-8. (Canceled)

9. (Currently Amended) A light emitting element comprising:

a first electrode and a second electrode;

a first layer and a second layer each generating holes;

a third layer containing a light emitting material; and

a fourth layer generating electrons,

wherein the first layer is in direct contact with the first electrode,

the second layer is in direct contact with the second electrode,

the third layer is provided between the first electrode and the second electrode with the first layer and the second layer respectively therebetween, and

the fourth layer is provided between the third layer and the second layer.

10. (Previously Presented) A light emitting element according to claim 9, wherein a thickness of each of the first layer and the second layer is 30 nm to 1 μ m.

11. (Previously Presented) A light emitting element according to claim 9, wherein a thickness of the second layer is 50 % to 150 % of a thickness of the first layer, and the thickness of the first layer is 50 % to 150 % of the thickness of the second layer.

12. (Original) A light emitting element according to claim 9, wherein t voltage is applied so as to make the light emitting element emit light, the electrode applied with higher potential is the first electrode, and the electrode applied with lower potential is the second electrode.

13. (Currently Amended) A light emitting element comprising:

a first electrode and a second electrode;

a first layer and a second layer each containing a P-type semiconductor;

a third layer containing a light emitting material; and

a fourth layer containing an N-type semiconductor,

wherein the first layer is in direct contact with the first electrode,

the second layer is in direct contact with the second electrode,

the third layer is provided between the first electrode and the second electrode with the first layer and the second layer respectively therebetween, and

the fourth layer is provided between the third layer and the second layer.

14. (Original) A light emitting element according to claim 13, wherein the P-type semiconductor is a metal oxide.

15. (Original) A light emitting element according to claim 13, wherein the P-type semiconductor is one or more compounds selected from the group consisting of vanadium oxide, molybdenum oxide, cobalt oxide, and nickel oxide.

16. (Original) A light emitting element according to claim 13, wherein the N-type semiconductor is a metal oxide.

17. (Original) A light emitting element according to claim 13, wherein the N-type semiconductor is one or more compounds selected from the group consisting of zinc oxide, zinc sulfide, zinc selenide, and titanium oxide.

18. (Previously Presented) A light emitting element according to claim 13, wherein a thickness of each of the first layer and the second layer is 30 nm to 1 μ m.

19. (Previously Presented) A light emitting element according to claim 13, wherein a thickness of the second layer is 50 % to 150 % of a thickness of the first layer, and the thickness of the first layer is 50 % to 150 % of the thickness of the second layer.

20. (Original) A light emitting element according to claim 13, wherein t voltage is applied so as to make the light emitting element emit light, the electrode applied with higher potential is the first electrode, and the electrode applied with lower potential is the second electrode.

21-31. (Canceled)

32. (Previously Presented) A light emitting element according to claim 9, wherein the light

emitting element is incorporated in one selected from the group consisting of a television, a mobile phone, a computer, and a game machine.

33. (Previously Presented) A light emitting element according to claim 13, wherein the light emitting element is incorporated in one selected from the group consisting of a television, a mobile phone, a computer, and a game machine.

34. (Currently Amended) A light emitting element comprising:

a first electrode over a substrate;

a first layer generating holes over and in direct contact with the first electrode;

a third layer containing a light emitting material over the first layer;

a fourth layer generating electrons over the third layer;

a second layer generating holes over the fourth layer; and

a second electrode over and in direct contact with the second layer.

35. (Previously Presented) A light emitting element according to claim 34, wherein a thickness of each of the first layer and the second layer is 30 nm to 1 μ m.

36. (Previously Presented) A light emitting element according to claim 34, wherein a thickness of the second layer is 50 % to 150 % of a thickness of the first layer, and the thickness of the first layer is 50 % to 150 % of the thickness of the second layer.

37. (Previously Presented) A light emitting element according to claim 34, wherein t voltage is applied so as to make the light emitting element emit light, the electrode applied with higher potential is the first electrode, and the electrode applied with lower potential is the second electrode.

38. (Previously Presented) A light emitting element according to claim 34, wherein the light emitting element is incorporated in one selected from the group consisting of a television, a mobile phone, a computer, and a game machine.

39. (Currently Amended) A light emitting element comprising:

- a first electrode over a substrate;
- a first layer containing a P-type semiconductor over and in direct contact with the first electrode;
- a third layer containing a light emitting material over the first layer;
- a fourth layer containing an N-type semiconductor over the third layer;
- a second layer containing a P-type semiconductor over the fourth layer; and
- a second electrode over and in direct contact with the second layer.

40. (Previously Presented) A light emitting element according to claim 39, wherein the P-type semiconductor is a metal oxide.

41. (Previously Presented) A light emitting element according to claim 39, wherein the P-type semiconductor is one or more compounds selected from the group consisting of vanadium oxide,

molybdenum oxide, cobalt oxide, and nickel oxide.

42. (Previously Presented) A light emitting element according to claim 39, wherein the N-type semiconductor is a metal oxide.

43. (Previously Presented) A light emitting element according to claim 39, wherein the N-type semiconductor is one or more compounds selected from the group consisting of zinc oxide, zinc sulfide, zinc selenide, and titanium oxide.

44. (Previously Presented) A light emitting element according to claim 39, wherein a thickness of each of the first layer and the second layer is 30 nm to 1 μ m.

45. (Previously Presented) A light emitting element according to claim 39, wherein a thickness of the second layer is 50 % to 150 % of a thickness of the first layer, and the thickness of the first layer is 50 % to 150 % of the thickness of the second layer.

46. (Previously Presented) A light emitting element according to claim 39, wherein a voltage is applied so as to make the light emitting element emit light, the electrode applied with higher potential is the first electrode, and the electrode applied with lower potential is the second electrode.

47. (Previously Presented) A light emitting element according to claim 39, wherein the light emitting element is incorporated in one selected from the group consisting of a television, a mobile

phone, a computer, and a game machine.